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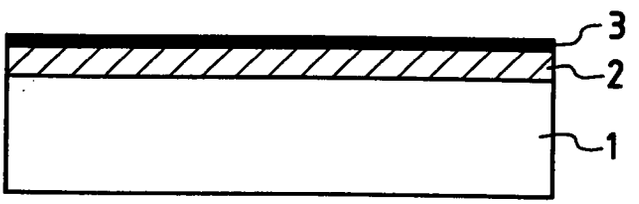
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(54) Semiconductor substrate and method for preparing it

(57) A semiconductor substrate comprises a plurality of substrates to be bonded, wherein a bond promotion layer into which silicon atoms are implanted is provided in an interface between the substrates to be bonded, and the substrates are bonded to each other with the interposition of the bond promotion layer.

FIG. 1A



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EUROPEAN SEARCH REPORT

Application Number
EP 93 11 3473

DOCUMENTS CONSIDERED TO BE RELEVANT

Category	Citation of document with indication, where appropriate, of relevant passages	Relevant to claim	CLASSIFICATION OF THE APPLICATION (Int.Cl.5)
A	GOETZ G G ET AL: "Generalized bonding" , 1989 IEEE SOS/SOI TECHNOLOGY CONFERENCE (CAT. NO.89CH2796-1), STATELINE, NV, USA, 3-5 OCT. 1989 , 1989, NEW YORK, NY, USA, IEEE, USA, PAGE(S) 125 - 126 XP000167660 * the whole document * ---	1,2,6	H01L21/20 H01L21/76
A	US 4 774 196 A (BLANCHARD RICHARD A) 27 September 1988 * claims 1,3,15 * ---	1,2	
A	DE 38 29 906 A (SIEMENS AG) 15 March 1990 * claims 1,2 * ---	1,2	
A	PROCEEDINGS OF TGHE 1992 INTERNATIONAL SYMPOSIUM ON POWER SEMICONDUCTOR DEVICES&IC'S. , TOKYO, pages 316-321, XP000340051 Y. SUGAWARA ET AL. : "NEW DIELECTRIC ISOLATION FOR HIGH VOLTAGE POWER ICS BY SINGLE SILICON POLY SILICON DIRECT BONDING (SPDB) TECHNIQUE" * the whole document * -----	1,2,6	

TECHNICAL FIELDS SEARCHED (Int.Cl.5)
H01L

The present search report has been drawn up for all claims

Place of search	Date of completion of the search	Examiner
THE HAGUE	18 July 1997	Vancraeynest, F

CATEGORY OF CITED DOCUMENTS

X : particularly relevant if taken alone
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